

TYPES 1N645, 1N646, 1N647, 1N648, 1N649 DIFFUSED SILICON HIGH POWER GLASS DIODE/RECTIFIERS



TYPES 1N645, 1N646, 1N647, 1N648, 1N649
BULLETIN NO. DL-S 1011, NOVEMBER, 1958
REPLACES BULLETIN NO. DL-S 770, JULY, 1957

400 MILLIAMPERES 225 to 600 VOLTS PIV

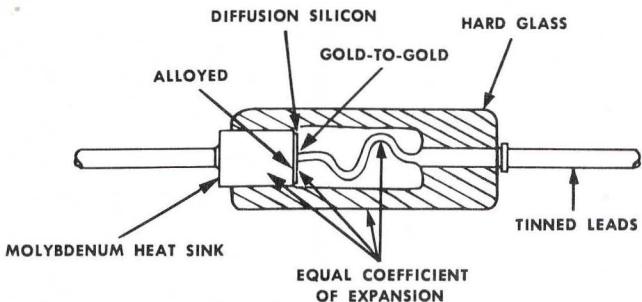
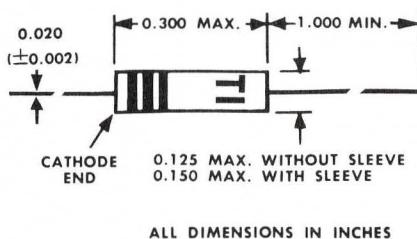
2-million-to-1 forward-to-reverse current ratio

Ruggedized to meet stringent military requirements
Designed for • magnetic amplifiers • modulators
demodulators • networks • power supplies



mechanical data

Hard glass hermetically sealed case with gold-to-gold contact. Unit weight is 0.195 gram.



maximum ratings

Peak Inverse Voltage at -65 to $+150^{\circ}\text{C}$	PIV
Average Rectified Forward Current at $+25^{\circ}\text{C}$	I_0
Average Rectified Forward Current at $+150^{\circ}\text{C}$	I_0
Recurrent Peak Forward Current at $+25^{\circ}\text{C}$	i_I
Power Dissipation at $+25^{\circ}\text{C}$	P
Surge Current, 1 Second at $+25$ to $+150^{\circ}\text{C}$	I_{DC}
Operating Temperature, Ambient	T_A
Altitude	

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Peak Inverse Voltage at -65 to $+150^{\circ}\text{C}$	225	300	400	500	600	V
Average Rectified Forward Current at $+25^{\circ}\text{C}$	400	400	400	400	400	mA
Average Rectified Forward Current at $+150^{\circ}\text{C}$	150	150	150	150	150	mA
Recurrent Peak Forward Current at $+25^{\circ}\text{C}$	1.25	1.25	1.25	1.25	1.25	amp
Power Dissipation at $+25^{\circ}\text{C}$	600	600	600	600	600	mW
Surge Current, 1 Second at $+25$ to $+150^{\circ}\text{C}$	3	3	3	3	3	Amp
Operating Temperature, Ambient	-65 to $+150$					$^{\circ}\text{C}$
Altitude	100,000					ft

specifications

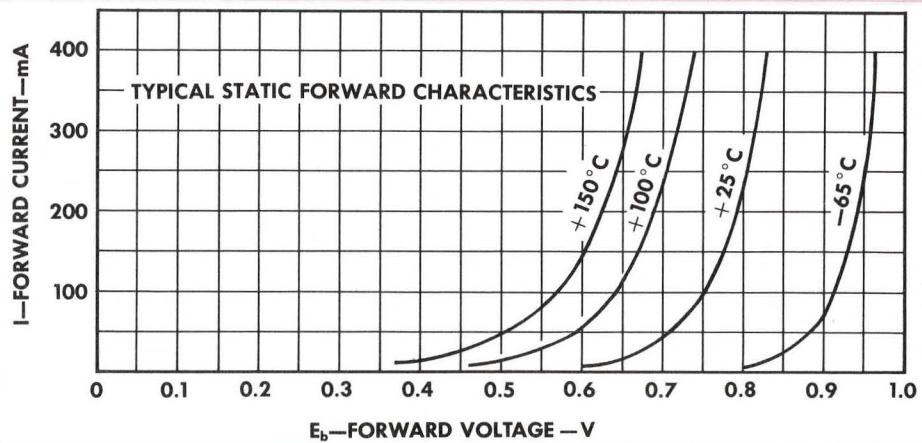
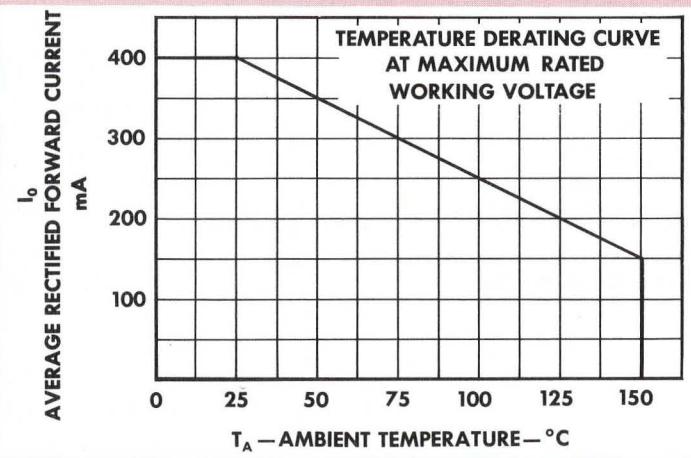
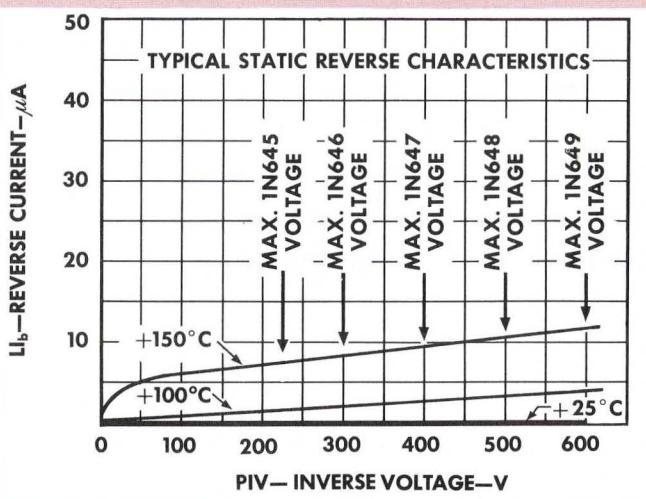
Minimum Breakdown Voltage at $+100^{\circ}\text{C}$	V_Z	275	360	480	600	720	V
Max. Reverse Current at PIV at $+25^{\circ}\text{C}$	I_{Rb}	0.2	0.2	0.2	0.2	0.2	μA
Max. Reverse Current at PIV at $+100^{\circ}\text{C}$	I_{Rb}	15	15	20	20	25	μA
Max. Voltage Drop at $I_b = 400 \text{ mA}$; at $+25^{\circ}\text{C}$	E_p	1.0	1.0	1.0	1.0	1.0	V
Typical Capacitance at -12V at 1 mc	C	9	9	9	9	9	$\mu\mu\text{f}$

LICENSED UNDER BELL SYSTEM PATENTS

SEMICONDUCTOR-COMPONENTS DIVISION

CHARACTERISTICS

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POST OFFICE BOX 312 • DALLAS, TEXAS

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